

Ai-Dong Li

List of Publications by Year in descending order

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197
papers

6,077
citations

94269

37
h-index

88477

70
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199
all docs

199
docs citations

199
times ranked

8815
citing authors

#	ARTICLE	IF	CITATIONS
1	Dual-Design of Nanoporous to Compact Interface via Atomic/Molecular Layer Deposition Enabling a Long-Life Silicon Anode. <i>Advanced Functional Materials</i> , 2022, 32, 2109682.	7.8	26
2	Role of atomic layer deposited TiOxNy interlayer in tribological and corrosion properties of CrN coating. <i>Surface and Coatings Technology</i> , 2022, 429, 127981.	2.2	3
3	Cobalt-Doping Stabilized Active and Durable Sub-2 nm Pt Nanoclusters for Low-Pt-Loading PEMFC Cathode. <i>Advanced Energy Materials</i> , 2022, 12, .	10.2	35
4	Cobalt-Doping Stabilized Active and Durable Sub-2 nm Pt Nanoclusters for Low-Pt-Loading PEMFC Cathode (Adv. Energy Mater. 13/2022). <i>Advanced Energy Materials</i> , 2022, 12, .	10.2	1
5	In Situ Formation of Polycyclic Aromatic Hydrocarbons as an Artificial Hybrid Layer for Lithium Metal Anodes. <i>Nano Letters</i> , 2022, 22, 263-270.	4.5	31
6	Design and self-catalytic mechanism of aluminum precursors bearing amino ligands for Al ₂ S ₃ atomic layer deposition. <i>Applied Surface Science</i> , 2022, 595, 153516.	3.1	4
7	Atomic Layer Deposition of High-Capacity Anodes for Next-Generation Lithium-Ion Batteries and Beyond. <i>Energy and Environmental Materials</i> , 2021, 4, 363-391.	7.3	43
8	Improved tribological properties and corrosion protection of CrN coating by ultrathin composite oxide interlayer. <i>Applied Surface Science</i> , 2021, 541, 148606.	3.1	21
9	A facile route to prepare TiO ₂ /g-C ₃ N ₄ nanocomposite photocatalysts by atomic layer deposition. <i>Journal of Alloys and Compounds</i> , 2021, 855, 157446.	2.8	27
10	±-Fe ₂ O ₃ /Ag/CdS ternary heterojunction photoanode for efficient solar water oxidation. <i>Catalysis Science and Technology</i> , 2021, 11, 5859-5867.	2.1	7
11	Core-shell MWCNTs@ZnS composite prepared by atomic layer deposition for high-performance lithium-ion batteries anode. <i>Journal of Materials Research</i> , 2021, 36, 1262-1271.	1.2	5
12	Tailoring Stress and Ion-Transport Kinetics via a Molecular Layer Deposition-Induced Artificial Solid Electrolyte Interphase for Durable Silicon Composite Anodes. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 32520-32530.	4.0	16
13	Highly stretchable and sensitive strain sensor based on silver nanowires/carbon nanotubes on hair band for human motion detection. <i>Progress in Natural Science: Materials International</i> , 2021, 31, 379-386.	1.8	13
14	Flexible Al-Ti-Zn-O MIM capacitors fabricated by room temperature atomic layer deposition and their electrical performances. <i>Journal of Alloys and Compounds</i> , 2021, 870, 159391.	2.8	7
15	Effect of Gd and Si co-doping on the band alignment and electrical properties of HfO ₂ dielectric films prepared by atomic layer deposition. <i>Journal of Materials Science: Materials in Electronics</i> , 2021, 32, 4815-4822.	1.1	0
16	Realizing the enhanced cyclability of a cactus-like NiCo ₂ O ₄ nanocrystal anode fabricated by molecular layer deposition. <i>Dalton Transactions</i> , 2021, 50, 511-519.	1.6	3
17	Polymerized hybrid Hf-based hydroquinone/Al ₂ O ₃ bilayer structure by molecular/atomic layer deposition for non-volatile resistive random access memory. <i>APL Materials</i> , 2021, 9, 121110.	2.2	6
18	Synaptic functions and a memristive mechanism on Pt/AlO _x /HfO _x /TiN bilayer-structure memristors. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 035302.	1.3	20

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19	Improved corrosion protection of CrN hard coating on steel sealed with TiOxNy-TiN composite layers. Surface and Coatings Technology, 2020, 381, 125108.	2.2	29
20	Simulation of Biologic Synapse Through Organic-Inorganic Hybrid Memristors Using Novel Ti-Based Maleic Acid/TiO ₂ Ultrathin Films. IEEE Electron Device Letters, 2020, 41, 155-158.	2.2	14
21	Conformal porous carbon coating on carbon fiber cloth/NiS ₂ composites by molecular layer deposition for durable supercapacitor electrodes. Journal of Materials Research, 2020, 35, 738-746.	1.2	9
22	Titanicone-derived TiO ₂ quantum dot@carbon encapsulated ZnO nanorod anodes for stable lithium storage. Dalton Transactions, 2020, 49, 10866-10873.	1.6	9
23	One-step facile preparation of zinc-based hydroquinone hybrid nanoporous thin films by molecular layer deposition. Applied Physics Letters, 2020, 117, 031601.	1.5	9
24	Optimization of oxygen vacancy concentration in HfO ₂ /HfOx bilayer-structured ultrathin memristors by atomic layer deposition and their biological synaptic behavior. Journal of Materials Chemistry C, 2020, 8, 12478-12484.	2.7	22
25	Enhanced visible light photocatalytic activity of Fe ₂ O ₃ modified TiO ₂ prepared by atomic layer deposition. Scientific Reports, 2020, 10, 13437.	1.6	59
26	High Visible-Light-Stimulated Plasticity in Optoelectronic Synaptic Transistors for Irradiation History-Dependent Learning. Advanced Electronic Materials, 2020, 6, 1901255.	2.6	13
27	Co-Pt bimetallic nanoparticles with tunable magnetic and electrocatalytic properties prepared by atomic layer deposition. Chemical Communications, 2020, 56, 8675-8678.	2.2	10
28	Combining Efficiency and Stability in Mixed Tin-Lead Perovskite Solar Cells by Capping Grains with an Ultrathin 2D Layer. Advanced Materials, 2020, 32, e1907058.	11.1	148
29	A stretchable petal patterned strain sensor comprising Ir nanoparticles-modified multi-walled carbon nanotubes for human-motion detection. Journal Physics D: Applied Physics, 2020, 53, 505402.	1.3	6
30	Review-Resistive-Type Hydrogen Sensors Based on Zinc Oxide Nanostructures. Journal of the Electrochemical Society, 2020, 167, 067528.	1.3	59
31	Atomic layer deposition of ZnO/TiO ₂ nanolaminates as ultra-long life anode material for lithium-ion batteries. Scientific Reports, 2019, 9, 11526.	1.6	38
32	Interface electron transfer and thickness dependent transport characteristics of La _{0.7} Sr _{0.3} VO ₃ thin films. Journal of Physics Condensed Matter, 2019, 31, 245002.	0.7	0
33	Comparison of chemical stability and corrosion resistance of group IV metal oxide films formed by thermal and plasma-enhanced atomic layer deposition. Scientific Reports, 2019, 9, 10438.	1.6	30
34	Atomic Layer-Deposited Al ₂ O ₃ Interlayer for Improved Tribological and Anti-corrosion Properties of TiN Hard Coating on 316L Stainless Steel. Journal of Materials Engineering and Performance, 2019, 28, 7058-7067.	1.2	4
35	Flexible Metal-Insulator Transitions Based on van der Waals Oxide Heterostructures. ACS Applied Materials & Interfaces, 2019, 11, 8284-8290.	4.0	35
36	Enhanced electrochemical performance of Ni-rich LiNi _{0.6} Co _{0.2} Mn _{0.2} O ₂ coated by molecular layer deposition derived dual-functional C-Al ₂ O ₃ composite coating. Journal of Alloys and Compounds, 2019, 799, 89-98.	2.8	43

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37	High-Performance MIM Capacitors Using Zr-Sn-Ti-O Dielectrics Derived from Atomic Layer Deposition. <i>IEEE Electron Device Letters</i> , 2019, 40, 682-685.	2.2	8
38	High-Performance Organic Field-Effect Transistor with Matching Energy-Band Alignment between Organic Semiconductor and the Charge-Trapping Dielectric. <i>Advanced Electronic Materials</i> , 2019, 5, 1800865.	2.6	7
39	Biomimetic strain sensors based on patterned polydimethylsiloxane and Ir nanoparticles decorated multi-walled carbon nanotubes. <i>Sensors and Actuators A: Physical</i> , 2019, 289, 57-64.	2.0	19
40	Growth Mechanism, Ambient Stability, and Charge Trapping Ability of Ti-Based Maleic Acid Hybrid Films by Molecular Layer Deposition. <i>Langmuir</i> , 2019, 35, 3020-3030.	1.6	10
41	Self-formed porous Ni(OH) ₂ on Ni ₃ S ₂ /Ni foam during electrochemical cycling for high performance supercapacitor with ultrahigh areal capacitance. <i>Electrochimica Acta</i> , 2019, 303, 148-156.	2.6	25
42	Band-alignment dominated retention behaviors in high-k composite charge-trapping memory devices. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	9
43	Monolithic all-perovskite tandem solar cells with 24.8% efficiency exploiting comproportionation to suppress Sn(ii) oxidation in precursor ink. <i>Nature Energy</i> , 2019, 4, 864-873.	19.8	736
44	Outstanding memory characteristics with atomic layer deposited Ta ₂ O ₅ /Al ₂ O ₃ /TiO ₂ /Al ₂ O ₃ /Ta ₂ O ₅ nanocomposite structures as the charge trapping layer. <i>Applied Surface Science</i> , 2019, 467-468, 423-427.	3.1	12
45	A comparative study of growth and properties of atomic layer deposited transparent conductive oxide of Al doped ZnO films from different Al precursors. <i>Thin Solid Films</i> , 2018, 646, 126-131.	0.8	24
46	Thermal atomic layer etching: Mechanism, materials and prospects. <i>Progress in Natural Science: Materials International</i> , 2018, 28, 667-675.	1.8	33
47	Impact of Metal Nanocrystal Size and Distribution on Resistive Switching Parameters of Oxide-Based Resistive Random Access Memories. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4674-4678.	1.6	10
48	Fabrication and Characterization of ZnO Nano-Clips by the Polyol-Mediated Process. <i>Nanoscale Research Letters</i> , 2018, 13, 47.	3.1	14
49	TiO _x N _y Modified TiO ₂ Powders Prepared by Plasma Enhanced Atomic Layer Deposition for Highly Visible Light Photocatalysis. <i>Scientific Reports</i> , 2018, 8, 12131.	1.6	21
50	Synaptic Plasticity and Learning Behaviors Mimicked in Single Inorganic Synapses of Pt/HfO _x /ZnO _x /TiN Memristive System. <i>Nanoscale Research Letters</i> , 2017, 12, 65.	3.1	46
51	Atomic Layer Deposited Oxide-Based Nanocomposite Structures with Embedded CoPt Nanocrystals for Resistive Random Access Memory Applications. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 6634-6643.	4.0	33
52	Giant tunnelling electroresistance in metal/ferroelectric/semiconductor tunnel junctions by engineering the Schottky barrier. <i>Nature Communications</i> , 2017, 8, 15217.	5.8	165
53	ZnO/ZnS Core-Shell Nanowires Arrays on Ni Foam Prepared by Atomic Layer Deposition for High Performance Supercapacitors. <i>Journal of the Electrochemical Society</i> , 2017, 164, A3493-A3498.	1.3	21
54	Atomic-Layer-Deposition Assisted Formation of Wafer-Scale Double-Layer Metal Nanoparticles with Tunable Nanogap for Surface-Enhanced Raman Scattering. <i>Scientific Reports</i> , 2017, 7, 5161.	1.6	18

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55	Interfacial, Electrical, and Band Alignment Characteristics of HfO ₂ /Ge Stacks with In Situ-Formed SiO ₂ Interlayer by Plasma-Enhanced Atomic Layer Deposition. <i>Nanoscale Research Letters</i> , 2017, 12, 370.	3.1	8
56	Bipolar Resistive Switching Characteristics of HfO ₂ /TiO ₂ /HfO ₂ Trilayer-Structure RRAM Devices on Pt and TiN-Coated Substrates Fabricated by Atomic Layer Deposition. <i>Nanoscale Research Letters</i> , 2017, 12, 393.	3.1	64
57	Improved electrochemical performance of Li _{1.2} Mn _{0.54} Ni _{0.13} Co _{0.13} O ₂ cathode material coated with ultrathin ZnO. <i>Journal of Alloys and Compounds</i> , 2017, 694, 848-856.	2.8	64
58	Photocatalytic Properties of Co ₃ O ₄ -Coated TiO ₂ Powders Prepared by Plasma-Enhanced Atomic Layer Deposition. <i>Nanoscale Research Letters</i> , 2017, 12, 497.	3.1	28
59	Visible Light-Driven Photocatalytic Performance of N-Doped ZnO/g-C ₃ N ₄ Nanocomposites. <i>Nanoscale Research Letters</i> , 2017, 12, 526.	3.1	69
60	Chemical strain-dependent two-dimensional transport at R_{AlO} interfaces		

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73	Atomic layer deposition of Co_3O_4 on carbon nanotubes/carbon cloth for high-capacitance and ultrastable supercapacitor electrode. <i>Nanotechnology</i> , 2015, 26, 094001.	1.3	84
74	Improved thermal stability and electrical properties of atomic layer deposited HfO_2/AlN high-k gate dielectric stacks on GaAs. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	4
75	Interface modulation and resistive switching evolution in $\text{Pt}/\text{NiO}_x/\text{Al}_2\text{O}_3/\text{n}^+\text{Si}$ structure. <i>Applied Physics A: Materials Science and Processing</i> , 2015, 118, 1365-1370.	1.1	2
76	Growth characteristics of Ti-based fumaric acid hybrid thin films by molecular layer deposition. <i>Dalton Transactions</i> , 2015, 44, 14782-14792.	1.6	24
77	Electromechanical Response from $\text{LaAlO}_3/\text{SrTiO}_3$ Heterostructures. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 10146-10151.	4.0	13
78	A facile and low-cost synthesis of $\text{Cu}_2\text{ZnSn}(\text{S Se})_4$ nanocrystals with tunable composition and optical band gap. <i>Materials Letters</i> , 2015, 150, 12-15.	1.3	13
79	Stepwise mechanism and H_2O -assisted hydrolysis in atomic layer deposition of SiO_2 without a catalyst. <i>Nanoscale Research Letters</i> , 2015, 10, 68.	3.1	10
80	Excellent resistive switching properties of atomic layer-deposited $\text{Al}_2\text{O}_3/\text{HfO}_2/\text{Al}_2\text{O}_3$ trilayer structures for non-volatile memory applications. <i>Nanoscale Research Letters</i> , 2015, 10, 135.	3.1	84
81	Integrated digital inverters based on two-dimensional anisotropic ReS_2 field-effect transistors. <i>Nature Communications</i> , 2015, 6, 6991.	5.8	505
82	Thickness-dependent metal-insulator transition in epitaxial SrRuO_3 ultrathin films. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	54
83	The Antibacterial Activity of Ta-doped ZnO Nanoparticles. <i>Nanoscale Research Letters</i> , 2015, 10, 1047.	3.1	141
84	Photocatalytic activity and photocorrosion of atomic layer deposited ZnO ultrathin films for the degradation of methylene blue. <i>Nanotechnology</i> , 2015, 26, 024002.	1.3	40
85	Growth of high-density Ir nanocrystals by atomic layer deposition for nonvolatile nanocrystal memory applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 042201.	0.6	5
86	The dominant factors affecting the memory characteristics of $(\text{Ta}_2\text{O}_5)_x(\text{Al}_2\text{O}_3)_{1-x}$ high-k charge-trapping devices. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	11
87	Monolayer FePt nanocrystal self-assembly embedded into atomic-layer-deposited Al_2O_3 films for nonvolatile memory applications. <i>Journal of Alloys and Compounds</i> , 2014, 588, 103-107.	2.8	8
88	Mechanical switching of ferroelectric polarization in ultrathin BaTiO_3 films: The effects of epitaxial strain. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	45
89	A facile way to deposit conformal Al_2O_3 thin film on pristine graphene by atomic layer deposition. <i>Applied Surface Science</i> , 2014, 291, 78-82.	3.1	19
90	Ferroelectric modulation on resonant tunneling through perovskite double-barriers. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	9

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91	Atomic layer deposition enhanced grafting of phosphorylcholine on stainless steel for intravascular stents. <i>Colloids and Surfaces B: Biointerfaces</i> , 2014, 121, 238-247.	2.5	21
92	Resistive switching in BiFeO_3 -based heterostructures due to ferroelectric modulation on interface Schottky barriers. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 3251-3256.	1.1	13
93	Fabrication and magnetic properties of FePt nanoparticle assemblies embedded in MgO-matrix systems. <i>Journal of Sol-Gel Science and Technology</i> , 2014, 71, 283-290.	1.1	5
94	Ti-Al-O nanocrystal charge trapping memory cells fabricated by atomic layer deposition. <i>Thin Solid Films</i> , 2014, 563, 6-9.	0.8	4
95	Nonvolatile memory capacitors based on Al_2O_3 tunneling and HfO_2 blocking layers with charge storage in atomic-layer-deposited Pt nanocrystals. <i>Applied Surface Science</i> , 2014, 289, 332-337.	3.1	19
96	Ultrathin ZnO coating for improved electrochemical performance of $\text{LiNi}_0.5\text{Co}_0.2\text{Mn}_0.3\text{O}_2$ cathode material. <i>Journal of Power Sources</i> , 2014, 266, 433-439.	4.0	212
97	The roles of the dielectric constant and the relative level of conduction band of high-k composite with Si in improving the memory performance of charge-trapping memory devices. <i>AIP Advances</i> , 2014, 4, 117110.	0.6	4
98	Atomic Layer Deposition of Al-doped ZnO Films Using Aluminum Isopropoxide as the Al Precursor. <i>Chemical Vapor Deposition</i> , 2013, 19, 180-185.	1.4	15
99	Temperature-dependent tunneling electroresistance in Pt/BaTiO ₃ /SrRuO ₃ ferroelectric tunnel junctions. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	31
100	Fabrication and magnetic properties of FePt/ Al_2O_3 composite film by atomic-layer-deposition. <i>Journal of Magnetism and Magnetic Materials</i> , 2013, 343, 1-5.	1.0	4
101	Preparation and visible-light photocatalytic properties of BiNbO ₄ and BiTaO ₄ by a citrate method. <i>Journal of Solid State Chemistry</i> , 2013, 202, 6-14.	1.4	59
102	Porous ZnO nanosheet arrays constructed on weaved metal wire for flexible dye-sensitized solar cells. <i>Nanoscale</i> , 2013, 5, 5102.	2.8	38
103	Facile synthesis of ultrafine $\text{Cu}_2\text{ZnSnS}_4$ nanocrystals by hydrothermal method for use in solar cells. <i>Thin Solid Films</i> , 2013, 535, 39-43.	0.8	42
104	Improved interfacial and electrical properties of atomic layer deposition HfO_2 films on Ge with La_2O_3 passivation. <i>Applied Surface Science</i> , 2013, 264, 783-786.	3.1	20
105	Impact of the interfaces in the charge trap layer on the storage characteristics of $\text{ZrO}_2/\text{Al}_2\text{O}_3$ nanolaminate-based charge trap flash memory cells. <i>Materials Letters</i> , 2013, 92, 21-24.	1.3	36
106	Bipolar resistive switching based on SrTiO ₃ /YBa ₂ Cu ₃ O ₇ epi-layers. <i>Journal Physics D: Applied Physics</i> , 2013, 46, 035308.	1.3	10
107	The metallic interface between insulating NdGaO_3 and SrTiO_3 perovskites. <i>Applied Physics Letters</i> , 2013, 103, 201602.	1.5	25
108	The effect of thermal treatment induced inter-diffusion at the interfaces on the charge trapping performance of $\text{HfO}_2/\text{Al}_2\text{O}_3$ nanolaminate-based memory devices. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	54

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109	First-Principles Study on Electronic Structure of Gd-Doped HfO ₂ High k Gate Dielectrics. Integrated Ferroelectrics, 2012, 134, 3-9.	0.3	8
110	Effects of Postannealing Temperature on the Band Alignments and Interfacial Properties of Atomic Layer Deposited Al ₂ O ₃ on Ge Substrates. Integrated Ferroelectrics, 2012, 134, 16-21.	0.3	1
111	Effect of annealing on interfacial and band alignment characteristics of HfO ₂ /SiO ₂ gate stacks on Ge substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 010602.	0.6	2
112	Characterization of HfO ₂ /Al ₂ O ₃ gate dielectric nanometer-stacks grown by atomic layer deposition on Ge substrates. , 2012, , .		2
113	Strain effects on magnetic characteristics of ultrathin La _{0.7} Sr _{0.3} MnO ₃ in epitaxial La _{0.7} Sr _{0.3} MnO ₃ /BaTiO ₃ superlattices. Journal of Applied Physics, 2012, 112, 123919.	1.1	14
114	The combination self-cleaning effect of trimethylaluminium and tetrakis (dimethyl-amino) hafnium pretreatments on GaAs. Applied Surface Science, 2012, 263, 497-501.	3.1	3
115	Synthesis and characterization of FePt nanoparticles and FePt nanoparticle/SiO ₂ -matrix composite films. Journal of Sol-Gel Science and Technology, 2012, 64, 269-275.	1.1	7
116	Preparation and magnetic properties of L ₁₀ -FePt/TiO ₂ nanocomposite thin films. Journal of Alloys and Compounds, 2012, 542, 128-131.	2.8	3
117	Surface Pseudorotation in Lewis-Base-Catalyzed Atomic Layer Deposition of SiO ₂ : Static Transition State Search and Born-Oppenheimer Molecular Dynamics Simulation. Journal of Physical Chemistry C, 2012, 116, 26436-26448.	1.5	22
118	Hf _x Zr _{1-x} O ₂ films chemical vapor deposited from a single source precursor of anhydrous Hf _x Zr _{1-x} (NO ₃) ₄ . Journal of Crystal Growth, 2012, 346, 12-16.	0.7	2
119	Magnetic and transport characteristics of long-period [(LaMnO ₃) _n /(SrMnO ₃) _n] _m superlattices. Journal of Applied Physics, 2012, 112, 103917.	1.1	2
120	Enhanced memory performance by tailoring the microstructural evolution of (ZrO ₂) _{0.6} (SiO ₂) _{0.4} charge trapping layer in the nanocrystallites-based charge trap flash memory cells. Applied Physics A: Materials Science and Processing, 2012, 108, 217-222.	1.1	15
121	Magnetic properties of FePt nanoparticle assemblies embedded in atomic-layer-deposited Al ₂ O ₃ . Journal of Materials Chemistry, 2011, 21, 5046.	6.7	23
122	Abnormal phase transition in BiNbO ₄ powders prepared by a citrate method. Journal of Alloys and Compounds, 2011, 509, 10230-10233.	2.8	31
123	Redox-controlled memristive switching in the junctions employing Ti reactive electrodes. AIP Advances, 2011, 1, 032141.	0.6	3
124	Band alignment and interfacial properties of atomic layer deposited (TiO ₂) _x (Al ₂ O ₃) _{1-x} gate dielectrics on Ge. Applied Physics A: Materials Science and Processing, 2011, 105, 763-767.	1.1	7
125	Effect of surface treatments on interfacial characteristics and band alignments of atomic-layer-deposited Al ₂ O ₃ films on GaAs substrates. Surface and Interface Analysis, 2011, 43, 734-737.	0.8	6
126	Effect of chemical surface treatments on interfacial and electrical characteristics of atomic-layer-deposited Al ₂ O ₃ films on Ge substrates. Applied Surface Science, 2011, 257, 4589-4592.	3.1	13

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127	Charge Trapping Memory Characteristics of p-Si/Ultrathin $\text{Al}_{2}\text{O}_{3}/(\text{HfO}_{2})_{x}(\text{Al}_{2}\text{O}_{3})_{1-x}$ /Metal Multilayer Structure. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, G13.	2.2	21
128	Fabrication and electrical characteristics of ultrathin $(\text{HfO}_{2})_{x}(\text{SiO}_{2})_{1-x}$ films by surface sol-gel method and reaction-anneal treatment. <i>Microelectronic Engineering</i> , 2010, 87, 1756-1759.	1.1	4
129	Photo-degradation of methylene blue using Ta-doped ZnO nanoparticle. <i>Journal of Solid State Chemistry</i> , 2010, 183, 1359-1364.	1.4	144
130	The roles of B-site ions in lead strontium zirconate titanate thin films for electrically tunable device applications. <i>Thin Solid Films</i> , 2010, 518, 3929-3932.	0.8	1
131	A $\text{TiAl}_{2}\text{O}_{5}$ nanocrystal charge trap memory device. <i>Applied Physics Letters</i> , 2010, 97, 143504.	1.5	37
132	Temperature-dependent leakage current characteristics of Pr and Mn cosubstituted BiFeO_{3} thin films. <i>Applied Physics Letters</i> , 2010, 96, 202904.	1.5	26
133	Impact of the Al/Hf ratio on the electrical properties and band alignments of atomic-layer-deposited $\text{HfO}_{2}/\text{Al}_{2}\text{O}_{3}$ on S-passivated GaAs substrates. <i>Semiconductor Science and Technology</i> , 2010, 25, 055012.	1.0	15
134	Properties of $\text{Hf}_{0.7}\text{Zr}_{0.3}\text{O}_{2}$ thin films chemical vapor deposited using a single-source precursor of anhydrous		

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145	Ferroelectric properties of bilayer structured Pb(Zr _{0.52} Ti _{0.48})O ₃ /SrBi ₂ Ta ₂ O ₉ (PZT/SBT) thin films on Pt/TiO ₂ /SiO ₂ /Si substrates. Applied Surface Science, 2008, 254, 1583-1586.	3.1	13
146	Transmission Electron Microscopy Observations on the Interfacial Structures of the Pt/SrBi ₂ Ta ₂ O ₉ /Pt Thin-Film Capacitors Prepared by Metallo-Organic Decomposition. Journal of the American Ceramic Society, 2008, 91, 979-985.	1.9	0
147	CHEMICAL VAPOR DEPOSITION OF Zr _x Hf _{1-x} O ₂ THIN FILMS USING ANHYDROUS MIXED-METAL NITRATES PRECURSORS. Integrated Ferroelectrics, 2008, 97, 93-102.	0.3	2
148	Polarization offset of homogeneous Bi _{3.15} Nd _{0.85} Ti ₃ O ₁₂ ferroelectric thin films. Journal of Applied Physics, 2008, 104, .	1.1	2
149	Polarization offsets of compositionally graded Nd-substituted Bi ₄ Ti ₃ O ₁₂ ferroelectric thin films. Applied Physics Letters, 2008, 93, 062904.	1.5	6
150	Structure and tuning properties of sol-gel-derived Pb _{0.4} Sr _{0.6} Zr _{0.52} Ti _{0.48} O ₃ (PSZT) thin films. Journal Physics D: Applied Physics, 2007, 40, 3793-3797.	1.3	8
151	PREPARATION AND CHARACTERIZATION OF POLED NANOCRYSTALS AND POLYMER COMPOSITE SrBi ₂ Ta ₂ O ₉ /PC FILMS. Integrated Ferroelectrics, 2007, 87, 59-66.	0.3	2
152	Effects of processing on all-optical poling characteristics of guest-host azo-dye polymer thin films. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 1114-1122.	0.8	6
153	A Novel Simple Route to Synthesize Aqueous Niobium and Tantalum Precursors for Ferroelectric and Photocatalytic Applications. Materials Research Society Symposia Proceedings, 2006, 942, 1.	0.1	10
154	Effect of an in-situ applied electric field on growth of Bi ₄ Ti ₃ O ₁₂ films by sol-gel. Applied Surface Science, 2006, 253, 1154-1159.	3.1	3
155	Chemical Vapor Deposition of Zr _x Ti _{1-x} O and Hf _x Ti _{1-x} O Thin Films Using the Composite Anhydrous Nitrate Precursors. Materials Research Society Symposia Proceedings, 2006, 917, 1.	0.1	0
156	Strontium-modified lead zirconate titanate thin films for electrically tunable device applications. Journal of Applied Physics, 2006, 100, 036102.	1.1	16
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